# **74AUP1T00**

Low-power 2-input NAND gate with voltage-level translator
Rev. 4 — 21 July 2023 Product data sheet

## 1. General description

The 74AUP1T00 provides the single 2-input NAND function. This device ensures a very low static and dynamic power consumption across the entire  $V_{CC}$  range from 2.3 V to 3.6 V.

The 74AUP1T00 is designed for logic-level translation applications with input switching levels that accept 1.8 V low-voltage CMOS signals, while operating from either a single 2.5 V or 3.3 V supply voltage.

The wide supply voltage range ensures normal operation as battery voltage drops from  $3.6\ V$  to  $2.3\ V$ .

This device is fully specified for partial power-down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

Schmitt trigger inputs make the circuit tolerant to slower input rise and fall times across the entire  $V_{CC}$  range.

#### 2. Features and benefits

- Wide supply voltage range from 2.3 V to 3.6 V
- High noise immunity
- Low static power consumption; I<sub>CC</sub> = 1.5 μA (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V<sub>CC</sub>
- I<sub>OFF</sub> circuitry provides partial power-down mode operation
- · ESD protection:
  - HBM: ANSI/ESDA/JEDEC JS-001 class 3A exceeds 5000 V
  - CDM: ANSI/ESDA/JEDEC JS-002 class C3 exceeds 1000 V
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

# 3. Ordering information

**Table 1. Ordering information** 

Type number	Package								
	Temperature range	Name	Description	Version					
74AUP1T00GW	-40 °C to +125 °C TSSOP5		plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1					
74AUP1T00GX	-40 °C to +125 °C	X2SON5	plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body 0.8 × 0.8 × 0.32 mm	SOT1226-3					



#### Low-power 2-input NAND gate with voltage-level translator

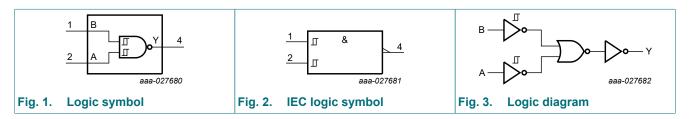
## 4. Marking

#### Table 2. Marking

Type number	Marking code [1]
74AUP1T00GW	5a
74AUP1T00GX	5a

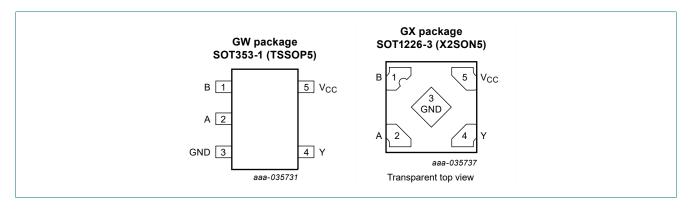
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

# 5. Functional diagram



# 6. Pinning information

## 6.1. Pinning



## 6.2. Pin description

Table 3. Pin description

Symbol	Pin	Description		
В	1	data input		
A	2	data input		
GND	3	ground (0 V)		
Υ	4	data output		
V <sub>CC</sub>	5	supply voltage		

#### Low-power 2-input NAND gate with voltage-level translator

## 7. Functional description

#### **Table 4. Function table**

 $H = HIGH \ voltage \ level; \ L = LOW \ voltage \ level.$ 

Input	Output	
A B		Υ
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

## 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CC</sub>	supply voltage			-0.5	+4.6	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < 0 V		-50	-	mA
VI	input voltage		[1]	-0.5	+4.6	V
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < 0 V		-50	-	mA
Vo	output voltage	Active mode and Power-down mode	[1]	-0.5	+4.6	V
Io	output current	V <sub>O</sub> = 0 V to V <sub>CC</sub>		-	±20	mA
I <sub>CC</sub>	supply current			-	50	mA
I <sub>GND</sub>	ground current			-50	-	mA
T <sub>stg</sub>	storage temperature			-65	+150	°C
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = -40 °C to +125 °C	[2]	-	250	mW

<sup>[1]</sup> The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

# 9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		2.3	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	V <sub>CC</sub>	V
		Power-down mode; V <sub>CC</sub> = 0 V	0	3.6	V
T <sub>amb</sub>	ambient temperature		-40	+125	°C

<sup>[2]</sup> For SOT353-1 (TSSOP5) package: P<sub>tot</sub> derates linearly with 3.3 mW/K above 74 °C. For SOT1226-3 (X2SON5) package: P<sub>tot</sub> derates linearly with 3.0 mW/K above 67 °C.

## Low-power 2-input NAND gate with voltage-level translator

## 10. Static characteristics

#### **Table 7. Static characteristics**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> = 2	5 °C					
V <sub>T+</sub>	positive-going threshold	V <sub>CC</sub> = 2.3 V to 2.7 V	0.60	-	1.10	V
	voltage	V <sub>CC</sub> = 3.0 V to 3.6 V	0.75	-	1.16	V
V <sub>T-</sub>	negative-going threshold	V <sub>CC</sub> = 2.3 V to 2.7 V	0.35	-	0.60	V
	voltage	V <sub>CC</sub> = 3.0 V to 3.6 V	0.50	-	0.85	V
V <sub>H</sub>	hysteresis voltage	$(V_{H} = V_{T+} - V_{T-})$				
		V <sub>CC</sub> = 2.3 V to 2.7 V	0.23	-	0.60	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	0.25	-	0.56	V
V <sub>OH</sub>	HIGH-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 2.3 V to 3.6 V	V <sub>CC</sub> - 0.1	-	-	V
		I <sub>O</sub> = -2.3 mA; V <sub>CC</sub> = 2.3 V	2.05	-	-	V
		I <sub>O</sub> = -3.1 mA; V <sub>CC</sub> = 2.3 V	1.9	-	-	V
		I <sub>O</sub> = -2.7 mA; V <sub>CC</sub> = 3.0 V	2.72	-	-	V
		$I_{O}$ = -4.0 mA; $V_{CC}$ = 3.0 V	2.6	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_{O}$ = 20 $\mu$ A; $V_{CC}$ = 2.3 $V$ to 3.6 $V$	-	-	0.10	V
		I <sub>O</sub> = 2.3 mA; V <sub>CC</sub> = 2.3 V	-	-	0.31	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.44	V
		I <sub>O</sub> = 2.7 mA; V <sub>CC</sub> = 3.0 V	-	-	0.31	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 3.0 V	-	-	0.44	V
l <sub>l</sub>	input leakage current	V <sub>I</sub> = GND to 3.6 V; V <sub>CC</sub> = 0 V to 3.6 V	-	-	±0.1	μΑ
I <sub>OFF</sub>	power-off leakage current	$V_{I}$ or $V_{O} = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.1	μΑ
Δl <sub>OFF</sub>	additional power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V to 0.2 V	-	-	±0.1	μΑ
I <sub>CC</sub>	supply current	V <sub>I</sub> = GND or V <sub>CC</sub> ; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 2.3 V to 3.6 V	-	-	1.2	μΑ
Cı	input capacitance	$V_{CC}$ = 0 V to 3.6 V; $V_I$ = GND or $V_{CC}$	-	0.8	-	pF
Co	output capacitance	$V_O = GND; V_{CC} = 0 V$	-	1.7	-	pF

## Low-power 2-input NAND gate with voltage-level translator

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> = -4	0 °C to +85 °C		<u> </u>	ı	1	
V <sub>T+</sub>	positive-going threshold	V <sub>CC</sub> = 2.3 V to 2.7 V	0.60	-	1.10	V
	voltage	V <sub>CC</sub> = 3.0 V to 3.6 V	0.75	-	1.19	V
V <sub>T-</sub>	negative-going threshold	V <sub>CC</sub> = 2.3 V to 2.7 V	0.35	-	0.60	V
	voltage	V <sub>CC</sub> = 3.0 V to 3.6 V	0.50	-	0.85	V
V <sub>H</sub>	hysteresis voltage	$(V_{H} = V_{T+} - V_{T-})$				
		V <sub>CC</sub> = 2.3 V to 2.7 V	0.10	-	0.60	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	0.15	-	0.56	V
V <sub>OH</sub>	HIGH-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_{O}$ = -20 $\mu$ A; $V_{CC}$ = 2.3 $V$ to 3.6 $V$	V <sub>CC</sub> - 0.1	-	-	V
		$I_{O}$ = -2.3 mA; $V_{CC}$ = 2.3 V	1.97	-	-	V
		$I_{O}$ = -3.1 mA; $V_{CC}$ = 2.3 V	1.85	-	-	V
		$I_{O}$ = -2.7 mA; $V_{CC}$ = 3.0 V	2.67	-	-	V
		$I_{O}$ = -4.0 mA; $V_{CC}$ = 3.0 V	2.55	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_{O}$ = 20 $\mu$ A; $V_{CC}$ = 2.3 V to 3.6 V	-	-	0.1	V
		$I_{O}$ = 2.3 mA; $V_{CC}$ = 2.3 V	-	-	0.33	V
		$I_{O}$ = 3.1 mA; $V_{CC}$ = 2.3 V	-	-	0.45	V
		$I_{O}$ = 2.7 mA; $V_{CC}$ = 3.0 V	-	-	0.33	V
		$I_{O}$ = 4.0 mA; $V_{CC}$ = 3.0 V	-	-	0.45	V
l <sub>l</sub>	input leakage current	$V_{I}$ = GND to 3.6 V; $V_{CC}$ = 0 V to 3.6 V	-	-	±0.5	μA
I <sub>OFF</sub>	power-off leakage current	$V_{I}$ or $V_{O}$ = 0 V to 3.6 V; $V_{CC}$ = 0 V	-	-	±0.5	μΑ
Δl <sub>OFF</sub>	additional power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V to 0.2 V	-	-	±0.5	μΑ
I <sub>CC</sub>	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A}; V_{CC} = 2.3 \text{ V to } 3.6 \text{ V}$	-	-	1.5	μA
$\Delta I_{CC}$	additional supply current	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V; } I_{O} = 0 \text{ A}$ [1]	-	-	0.6	μΑ
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V; } I_{O} = 0 \text{ A}$ [2]	-	-	10	μΑ
		1 -	I	I	1	

## Low-power 2-input NAND gate with voltage-level translator

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> = -4	0 °C to +125 °C				1	
V <sub>T+</sub>	positive-going threshold	V <sub>CC</sub> = 2.3 V to 2.7 V	0.60	-	1.10	V
	voltage	V <sub>CC</sub> = 3.0 V to 3.6 V	0.75	-	1.19	V
V <sub>T-</sub>	negative-going threshold	V <sub>CC</sub> = 2.3 V to 2.7 V	0.33	-	0.64	V
	voltage	V <sub>CC</sub> = 3.0 V to 3.6 V	0.46	-	0.85	V
V <sub>H</sub>	hysteresis voltage	$(V_{H} = V_{T+} - V_{T-})$				
		V <sub>CC</sub> = 2.3 V to 2.7 V	0.10	-	0.60	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	0.15	-	0.56	V
V <sub>OH</sub>	HIGH-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_{O}$ = -20 $\mu$ A; $V_{CC}$ = 2.3 $V$ to 3.6 $V$	V <sub>CC</sub> - 0.11	-	-	V
		$I_{O}$ = -2.3 mA; $V_{CC}$ = 2.3 V	1.77	-	-	V
		$I_{O}$ = -3.1 mA; $V_{CC}$ = 2.3 V	1.67	-	-	V
		$I_{O}$ = -2.7 mA; $V_{CC}$ = 3.0 V	2.40	-	-	V
		$I_{O}$ = -4.0 mA; $V_{CC}$ = 3.0 V	2.30	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_{O}$ = 20 $\mu$ A; $V_{CC}$ = 2.3 V to 3.6 V	-	-	0.11	V
		$I_{O}$ = 2.3 mA; $V_{CC}$ = 2.3 V	-	-	0.36	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.50	V
		$I_{O}$ = 2.7 mA; $V_{CC}$ = 3.0 V	-	-	0.36	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 3.0 V	-	-	0.50	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = GND to 3.6 V; V <sub>CC</sub> = 0 V to 3.6 V	-	-	±0.75	μA
I <sub>OFF</sub>	power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V	-	-	±0.75	μΑ
Δl <sub>OFF</sub>	additional power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V to 0.2 V	-	-	±0.75	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = GND or V <sub>CC</sub> ; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 2.3 V to 3.6 V	-	-	3.5	μΑ
ΔI <sub>CC</sub>	additional supply current	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V; } I_O = 0 \text{ A}$ [1]	-	-	1.8	μΑ
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V; } I_O = 0 \text{ A}$ [2]	-	-	18	μΑ
		V() 0.0 V to 0.0 V, 10 = 0 /1 [2]	_	_	10	

One input at 0.3 V or 1.1 V, other input at  $V_{CC}$  or GND. One input at 0.45 V or 1.2 V, other input at  $V_{CC}$  or GND.

## Low-power 2-input NAND gate with voltage-level translator

# 11. Dynamic characteristics

#### **Table 8. Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 5.

Symbol	Parameter	Conditions		25 °C		-40 °C to	o +85 °C	-40 °C to	+125 °C	Unit
			Min	Typ[1]	Max	Min	Max	Min	Max	
V <sub>CC</sub> = 2.	3 V to 2.7 V; V <sub>I</sub>	= 1.65 V to 1.95 V		·			I		ı	
t <sub>pd</sub>	propagation	A, B to Y; see <u>Fig. 4</u> [2]								
	delay	C <sub>L</sub> = 5 pF	1.9	3.4	5.3	0.5	6.8	0.5	7.5	ns
		C <sub>L</sub> = 10 pF	2.4	3.9	6.0	1.0	7.9	1.0	8.7	ns
		C <sub>L</sub> = 15 pF	2.8	4.4	6.6	1.0	8.7	1.0	9.6	ns
		C <sub>L</sub> = 30 pF	3.8	5.6	8.0	1.5	10.8	1.5	11.9	ns
$V_{CC} = 2.$	3 V to 2.7 V; V <sub>I</sub>	= 2.3 V to 2.7 V								
t <sub>pd</sub>	propagation	A, B to Y; see <u>Fig. 4</u> [2]								
	delay	C <sub>L</sub> = 5 pF	1.4	3.2	5.3	0.5	6.0	0.5	6.6	ns
		C <sub>L</sub> = 10 pF	1.9	3.8	6.0	1.0	7.1	1.0	7.9	ns
		C <sub>L</sub> = 15 pF	2.3	4.3	6.6	1.0	7.9	1.0	8.7	ns
		C <sub>L</sub> = 30 pF	3.4	5.5	8.0	1.5	10.0	1.5	11.0	ns
$V_{CC} = 2.$	3 V to 2.7 V; V <sub>I</sub>	= 3.0 V to 3.6 V								
t <sub>pd</sub>	propagation	A, B to Y; see <u>Fig. 4</u> [2]								
	delay	C <sub>L</sub> = 5 pF	1.2	3.0	4.8	0.5	5.5	0.5	6.1	ns
		C <sub>L</sub> = 10 pF	1.6	3.5	5.5	1.0	6.5	1.0	7.2	ns
		C <sub>L</sub> = 15 pF	2.1	4.0	6.1	1.0	7.4	1.0	8.2	ns
		C <sub>L</sub> = 30 pF	3.1	5.2	7.5	1.5	9.5	1.5	10.5	ns
$V_{CC} = 3.$	0 V to 3.6 V; V <sub>I</sub>	= 1.65 V to 1.95 V								
$t_{pd}$	propagation	A, B to Y; see <u>Fig. 4</u> [2]	l							
	delay	C <sub>L</sub> = 5 pF	1.9	2.8	3.9	0.5	8.0	0.5	9.0	ns
		C <sub>L</sub> = 10 pF	2.3	3.4	4.7	1.0	8.5	1.0	9.4	ns
		C <sub>L</sub> = 15 pF	2.6	3.8	5.3	1.0	9.1	1.0	10.1	ns
		C <sub>L</sub> = 30 pF	3.4	5.0	6.8	1.5	9.8	1.5	10.8	ns
$V_{CC} = 3.$	0 V to 3.6 V; V <sub>I</sub>	= 2.3 V to 2.7 V								
$t_{pd}$	propagation	A, B to Y; see <u>Fig. 4</u> [2]	l							
	delay	C <sub>L</sub> = 5 pF	1.4	2.7	4.2	0.5	5.3	0.5	5.9	ns
		C <sub>L</sub> = 10 pF	1.9	3.3	4.9	1.0	6.1	1.0	6.8	ns
		C <sub>L</sub> = 15 pF	2.3	3.7	5.5	1.0	6.8	1.0	7.5	ns
		C <sub>L</sub> = 30 pF	3.3	4.9	6.8	1.5	8.5	1.5	9.4	ns
$V_{CC} = 3.$	0 V to 3.6 V; V <sub>I</sub>	= 3.0 V to 3.6 V								
$t_{pd}$	propagation	A, B to Y; see <u>Fig. 4</u> [2]								
	delay	C <sub>L</sub> = 5 pF	1.0	2.6	4.3	0.5	4.7	0.5	5.2	ns
		C <sub>L</sub> = 10 pF	1.6	3.2	5	1.0	5.7	1.0	6.3	ns
		C <sub>L</sub> = 15 pF	2.0	3.7	5.6	1.0	6.2	1.0	6.9	ns
		C <sub>L</sub> = 30 pF	3.0	4.8	6.9	1.5	7.8	1.5	8.6	ns

#### Low-power 2-input NAND gate with voltage-level translator

Symbol	Parameter	Conditions	25 °C		25 °C -40 °C to +85 °C -		-40 °C to +125 °C		Unit	
			Min	Typ[1]	Max	Min	Max	Min	Max	
T <sub>amb</sub> = 2	T <sub>amb</sub> = 25 °C									
C <sub>PD</sub>	power	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$ [3]								
	dissipation capacitance	V <sub>CC</sub> = 2.3 V to 2.7 V	-	4	-	-	-	-	-	pF
	oapaolarioc	V <sub>CC</sub> = 3.0 V to 3.6 V	-	5	-	-	_	-	-	pF

- All typical values are measured at nominal V<sub>CC</sub>.
- $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$   $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu$ W).  $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$  where:

f<sub>i</sub> = input frequency in MHz;

f<sub>o</sub> = output frequency in MHz;

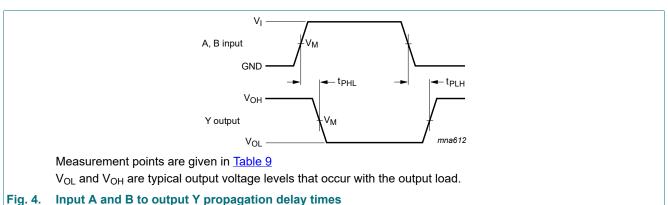
C<sub>L</sub> = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_0)$  = sum of the outputs.

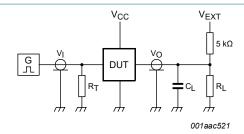
#### 11.1. Waveforms and test circuit



**Table 9. Measurement points** 

Supply voltage	Output	Input					
V <sub>CC</sub>	V <sub>M</sub>	$V_{\rm M}$ $V_{\rm I}$ $t_{\rm r} = t_{\rm f}$					
2.3 V to 3.6 V	0.5 × V <sub>CC</sub>	0.5 × V <sub>I</sub>	1.65 V to 3.6 V	≤ 3.0 ns			

### Low-power 2-input NAND gate with voltage-level translator



Test data is given in Table 10.

Definitions for test circuit:

R<sub>L</sub> = Load resistance;

C<sub>L</sub> = Load capacitance including jig and probe capacitance;

R<sub>T</sub> = Termination resistance should be equal to the output impedance Zo of the pulse generator;

V<sub>EXT</sub> = External voltage for measuring switching times.

#### Fig. 5. Test circuit for measuring switching times

#### Table 10. Test data

Supply voltage	Load		V <sub>EXT</sub>		
V <sub>CC</sub>	CL	R <sub>L</sub> [1]	t <sub>PLH</sub> , t <sub>PHL</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub>
2.3 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	2 × V <sub>CC</sub>

[1] For measuring enable and disable times  $R_L$  = 5 k $\Omega$ . For measuring propagation delays, setup and hold times and pulse width  $R_L$  = 1 M $\Omega$ .

#### Low-power 2-input NAND gate with voltage-level translator

# 12. Package outline

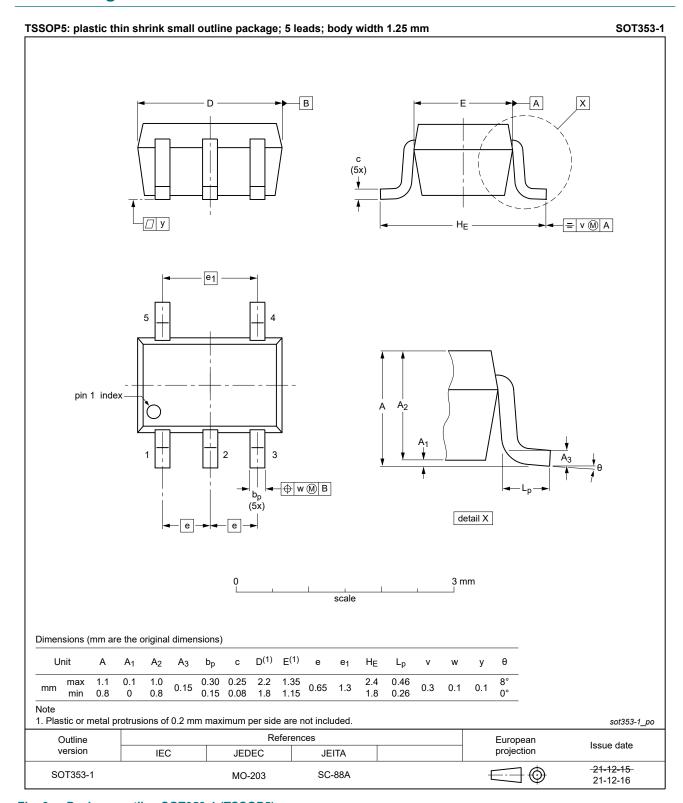


Fig. 6. Package outline SOT353-1 (TSSOP5)

#### Low-power 2-input NAND gate with voltage-level translator

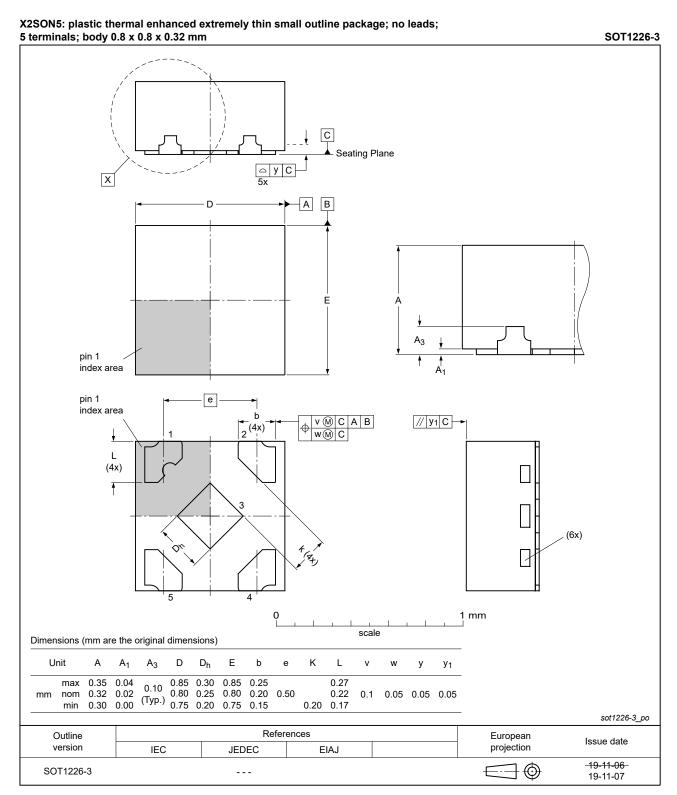


Fig. 7. Package outline SOT1226-3 (X2SON5)

## Low-power 2-input NAND gate with voltage-level translator

## 13. Abbreviations

#### **Table 11. Abbreviations**

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model

# 14. Revision history

#### Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
74AUP1T00 v.4	20230721	Product data sheet	-	74AUP1T00 v.3	
Modifications:	<u>Section 2</u> : ESD specification updated according to the latest JEDEC standard.				
74AUP1T00 v.3	20220125	Product data sheet	-	74AUP1T00 v.2	
Modifications:	Fig. 6: Package outline drawing for SOT353-1 has changed.				
74AUP1T00 v.2	20210719	Product data sheet	-	74AUP1T00 v.1	
Modifications:	<ul> <li>SOT1226 (X2SON5) package changed to SOT1226-3 (X2SON5) package.</li> <li>Table 5: Derating values for P<sub>tot</sub> total power dissipation updated.</li> </ul>				
74AUP1T00 v.1	20171123	Product data sheet	-	-	

#### Low-power 2-input NAND gate with voltage-level translator

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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## Low-power 2-input NAND gate with voltage-level translator

## **Contents**

1. General description	1
2. Features and benefits	1
3. Ordering information	1
4. Marking	2
5. Functional diagram	2
6. Pinning information	2
6.1. Pinning	2
6.2. Pin description	2
7. Functional description	3
8. Limiting values	3
9. Recommended operating conditions	3
10. Static characteristics	4
11. Dynamic characteristics	7
11.1. Waveforms and test circuit	8
12. Package outline	10
13. Abbreviations	12
14. Revision history	12
15. Legal information	13

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